

Panasonic

FK8V03060L

Silicon N-channel MOS FET

For lithium-ion secondary battery protection circuit

For DC-DC Converter

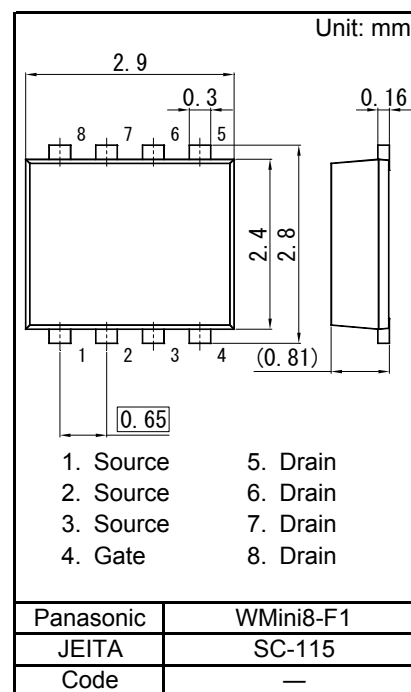
■ Features

- Low drain-source On-state Resistance
RDS(on) typ. = 22 mΩ (VGS = 4.5 V)
- High-speed switching : Qg = 3.8 nC
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol: 3F

■ Packaging

Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)



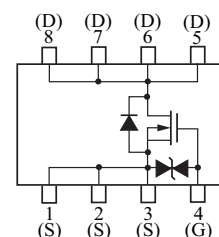
■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain-source Voltage	VDS	33	V
Gate-source Voltage	VGS	±20	V
Drain Current (Steady State) ^{*1}	ID	6.5	A
Drain Current (t = 10 s) ^{*1}		8	
Drain Current (Pulsed) ^{*1,*2}		26	
Source Current (Pulsed) (Body Diode) ^{*1,*2}	ISp (BD)	6.5	W
Total Power Dissipation (Steady State) ^{*1}	PD	1	
Total Power Dissipation (t = 10 s) ^{*1}		1.5	
Channel Temperature	Tch	150	°C
Operating Ambient Temperature	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Note) ^{*1} Device mounted on a glass-epoxy board (See Figure 1)

^{*2} Pulse test: Ensure that the channel temperature does not exceed 150°C

Internal Connection



Pin Name

- | | |
|-----------|----------|
| 1. Source | 5. Drain |
| 2. Source | 6. Drain |
| 3. Source | 7. Drain |
| 4. Gate | 8. Drain |

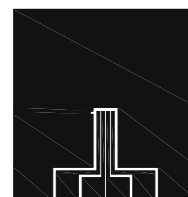


Figure1 FR4 Glass-Epoxy Board
25.4 mm × 25.4 mm × 0.8 mm